

Electronics for Computer Engineering

Submit عند إنهاء الإجابة على كامل الاسئلة يجب تسليم اجابتك بالضغط على

مرحباً محمد، عند إرسال هذا النموذج، سيُرى مالك النموذج اسمك وبريدك الإلكتروني.

* مطلوب

1

* If the BJT transistor in CE configuration is in saturation then
(2 نقطة)

☒ *I_C is always equal to βI_B*

☐ *I_C is always equal to $-\beta I_B$*

☐ *I_C is greater than or equal to βI_B*

☐ *I_C is less than βI_B*

2

* ?Which of the following ratings is true
(2 نقطة)

☐ Si diodes have higher PIV and narrower temperature ranges than Ge diodes

☒ Si diodes have higher PIV and wider temperature ranges than Ge diodes

☐ Si diodes have lower PIV and narrower temperature ranges than Ge diodes

☐ Si diodes have lower PIV and wider temperature ranges than Ge diodes

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* a.....circuit is a circuit which shifts the DC level of output voltage
(1 نقطة)

☐ Clipper

☒ Clamper

☐ Rectifier

☐ Regulator

4

* ?What is the level of I_G in a MOSFET
(2 نقطة)

☒ Zero amperes

☐ Equal to I_D

☐ Depends on V_{DS}

☐ $I_D = I_S$

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The depletion width _____ in the forward bias, which results in having a majority flow across
* .the junction
(1 نقطة)

☐ increases

☐ remains unchanged

☒ reduces

6

* The number of carriers participating in the operation principle of a unipolar device is (2 نقطة)

- 3 ☐
- 1 ☒
- 0 ☐
- 2 ☐

7

* ?Which of the following is (are) the application(s) of a transistor (2 نقطة)

- Computer logic circuitry ☐
- Switching and control ☐
- All ☒
- Amplification of signal ☐

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which one of the stability factors has the least impact on the device at a very high temperature
* ?in a voltage-divider biasing network of BJT amplifier (2 نقطة)

- $S(\beta)$ ☒
- $S(I_{CO})$ ☐
- Undefined ☐
- $S(V_{BE})$ ☐
- $S(I_{BO})$ ☐

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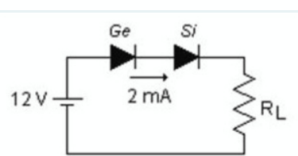
*.The inner layer of a BJT transistor is _____ the outer layers (2 نقطة)

- much smaller than ☒
- the same as ☐
- much larger than ☐
- None of the above ☐

10

*.Determine the value of α when $\beta = 100$ (2 نقطة)

- 0.01 ☐
- 101 ☐
- 0.99 ☒
- Cannot be solved ☐



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*.Determine the resistor R_L (2 نقطة)

$R_L = 16\text{ k}\Omega$ ☐

$R_L = 5\text{ k}\Omega$ ☐

$R_L = 15\text{ k}\Omega$ ☐

None of the above ☒

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*The ratio of the total swing of the output of a clamper to its input peak-peak value is (2 نقطة)

1 ☒

0.5 ☐

2 ☐

0 ☐

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The slope of the dc load line in a voltage-divider network in a common sources FET .48
* amplifier is controlled by (2 نقطة)

R_1 ☒

V_{BE} ☐

I_{DSS} ☒

V_P ☐

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* To increase the current-carrying capability, practical diodes are connected (2 نقطة)

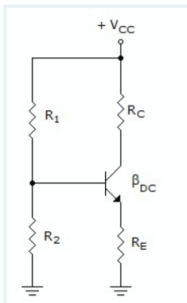
in parallel ☒

in series ☐

in parallel-series ☐

None of the above ☐

15



* In the voltage-divider biased NPN transistor circuit, if R_1 opens, the transistor is (2 نقطة)

operates in the saturation region ☐

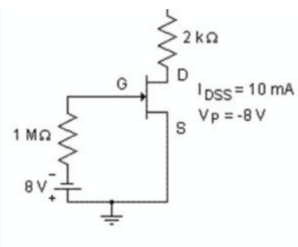
operates in the cut off region ☐

operates in the active region ☒

.can not be determined ☐

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* The maximum current that can flow in the 2 k ohm is
(2 نقطة)

- 10mA ☒
- 1.1mA ☐
- 2mA ☐
- can not be solved ☐

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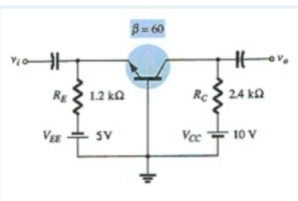
* ____ As the load resistor decreases, the levels of diode operating current
(2 نقطة)

- decrease ☒
- remain unchanged ☐
- increase ☐
- are unpredictable ☐

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* The E-MOSFET is a ____ controlled device and npn transistor is a ____ controlled device
(2 نقطة)

- voltage, current ☐
- current, voltage ☐
- None of the options ☐
- current, current ☐
- voltage, voltage ☒



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* .Determine the values of V_{BC} and I_B for this circuit
(2 نقطة)

- V, 3.58 μA 9.3 ☐
- V, 58.7 μA 1.4- ☐
- cannot be solved ☐
- V, 58.7 μA 1.4 ☒
- V, 3.58 μA 9.3- ☐

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* ____ The dc load line of the common base amplifier is determined solely by the
(2 نقطة)

base-collector loop ☒

base-emitter loop ☐

None ☐

collector-emitter loop ☐

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* _____ to increase the total PIV rating, diodes are connected
(2 نقطة)

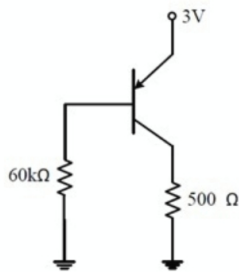
None of the above ☐

in parallel ☐

in parallel-series ☐

in series ☒

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the BJT has a current gain (β) of 50. For an emitter – base voltage $V_{EB} = 0.7V$, the emitter –
* _____ collector voltage V_{CE} (in Volts) is
(2 نقطة)

2.04V- ☒

2.04V ☐

can not be solved ☐

2.14- ☐

2.14 ☐

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* The capacitors are used to _____ in amplifier configurations
(2 نقطة)

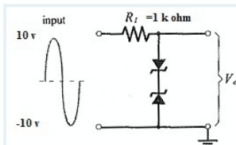
block the dc level ☒

allow dc level ☐

to shift the Q point ☐

All of the options ☐

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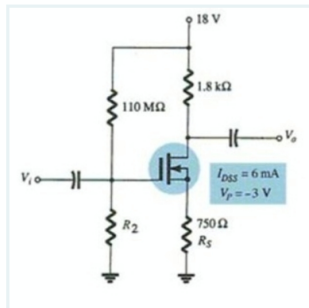
Determine the peak for both half cycles of the output waveform, if the Zener diodes have
* $V_Z = 10V$ and fabricated from Silicon
(2 نقطة)

$V_o = -10.7V$ to $10.7V$ ☒

v_i = 0.7 v 0.7 ☐

v_i = 9.3 v 9.3 ☐

can not be solved ☐



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* ?what is the value of R2 that makes VGSQ equal to 1 V
(2 نقطة)

MΩ 10 ☐

MΩ 100 ☐

MΩ 110 ☒

MΩ 22 ☐

None ☐

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* . in the Zener diode, changing the _____ can vary the value of V_Z
(2 نقطة)

the load resistance ☐

the input voltage ☐

leakage current ☐

forward voltage ☐

doping concentration ☒

إرسال

تم إنشاء هذا المحتوى بواسطة مالك النموذج. سيتم إرسال البيانات التي ترسلها إلى مالك النموذج. لا تعطي كلمة المرور الخاصة بك لأحد.

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